TOSHIBA 1DL41A

TOSHIBA HIGH EFFICIENCY RECTIFIER (HED) SILICON EPITAXIAL JUNCTION TYPE

# D L 4 1 A

### SWITCHING TYPE POWER SUPPLY APPLICATIONS

Repetitive Peak Reverse Voltage  $: V_{RRM} = 200 V$ 

Average Forward Current  $: I_{F(AV)} = 1.0 \text{ A (Ta} = 64^{\circ}\text{C)}$ 

Very Fast Reverse-Recovery Time :  $t_{rr} = 35 \text{ ns}$  (Max.)

Low Forward Voltage  $: V_{FM} = 0.98 V \text{ (Max.)}$ 

Available to Reduce Switching Losses and Output Noise.

#### **MAXIMUM RATINGS**

CHARACTERISTIC	SYMBOL	RATING	UNIT	
Repetitive Peak Reverse Voltage	$v_{RRM}$	200	V	
Average Forward Current (Ta = 64°C)	I <sub>F (AV)</sub>	1.0	A	
Peak One Cycle Surge Forward	Incre	30 (50 Hz)	Α	
Current (Non-Repetitive)	$I_{FSM}$	33 (60 Hz)	A	
Junction Temperature	$T_{j}$	-40~150	$^{\circ}\mathrm{C}$	
Storage Temperature Range	$\mathrm{T_{stg}}$	-40~150	°C	

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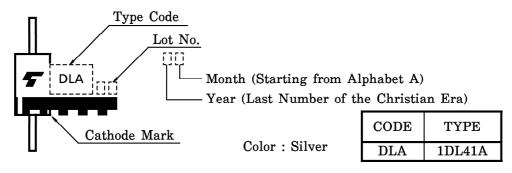
Unit in mm

Weight: 0.225 g

## ELECTRICAL CHARACTERISTICS (Ta = 25°C)

CHARACTERISTIC	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Peak Forward Voltage	$ m V_{FM}$	$I_{\text{FM}} = 1.0 \text{ A}$	_	_	0.98	V
Repetitive Peak Reverse Current	$I_{RRM}$	$V_{RRM} = 200 V$		_	100	$\mu$ <b>A</b>
Reverse Recovery Time	$t_{rr}$	$I_F = 1 A$ , $di/dt = -30 A/\mu s$		_	35	ns
Forward Recovery Time	$t_{fr}$	$I_{\mathrm{F}} = 1.0 \mathrm{A}$	_	_	100	ns
Thermal Resistance	R <sub>th (j-a)</sub>	Junction to Ambient	_		115	°C/W
Thermal Resistance	$R_{ ext{th }(j-\ell)}$	Junction to Lead	_	_	45	°C/W

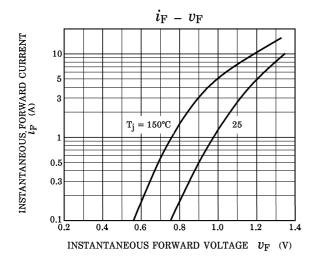
## **MARKING**

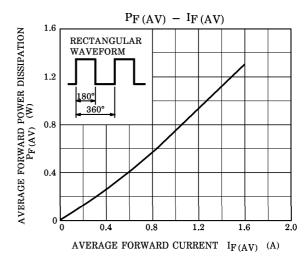


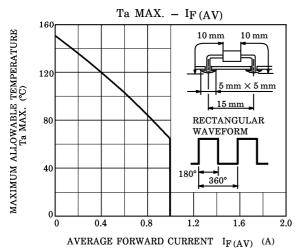
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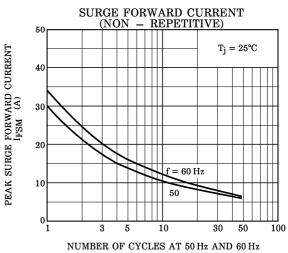
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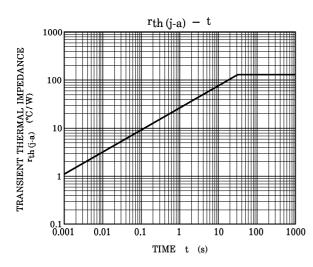
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